STB25NM60Nx - STF25NM60N
STP25NM60N - STW25NM60N

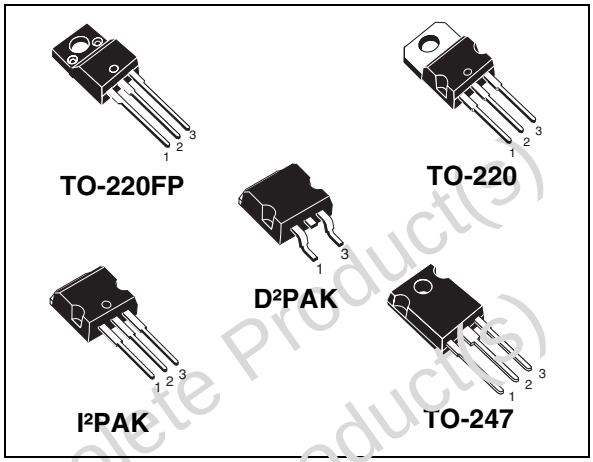
N-channel 600 V, 0.130 Ω , 21 A, MDmesh™ II Power MOSFET
TO-220, TO-220FP, I²PAK, D²PAK, TO-247

Features

Type	V_{DSS} (@Tjmax)	$R_{DS(on)}$ max	I_D
STB25NM60N	650 V	< 0.160 Ω	21 A
STB25NM60N-1	650 V	< 0.160 Ω	21 A
STF25NM60N	650 V	< 0.160 Ω	21 A(1)
STP25NM60N	650 V	< 0.160 Ω	21 A
STW25NM60N	650 V	< 0.160 Ω	21 A

1. Limited only by maximum temperature allowed

- 100% avalanche tested
- Low input capacitance and gate charge
- Low gate input resistance



Application

- Switching applications

Description

This series of devices is realized with the second generation of MDmesh™ technology. This revolutionary MOSFET associates a new vertical structure to the company's strip layout to yield one of the world's lowest on-resistance and gate charge. It is therefore suitable for the most demanding high efficiency converters

Figure 1. Internal schematic diagram

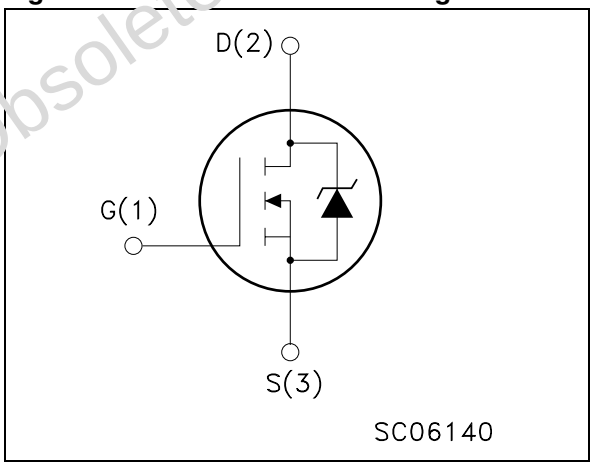


Table 1. Device summary

Order codes	Marking	Package	Packaging
STB25NM60N	B25NM60N	D²PAK	Tape and reel
STB25NM60N-1	B25NM60N	I²PAK	Tube
STF25NM60N	F25NM60N	TO-220FP	Tube
STP25NM60N	P25NM60N	TO-220	Tube
STW25NM60N	W25NM60N	TO-247	Tube

Contents

1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value		Unit
		TO-220 - I²PAK D²PAK - TO-247	TO-220FP	
V_{DS}	Drain-source voltage (V_{GS} = 0)	600		V
V_{GS}	Gate- source voltage	±25		V
I_D	Drain current (continuous) at T_C = 25 °C	21	21 (1)	A
I_D	Drain current (continuous) at T_C = 100 °C	13	13 (1)	A
I_{DM} (2)	Drain current (pulsed)	84	84 (1)	A
P_{TOT}	Total dissipation at T_C = 25 °C	160	40	W
V_{ISO}	Insulation withstand voltage (RMS) from all three leads to external heat sink (t=1 s;T_C=25 °C)	--	2500	V
dv/dt (3)	Peak diode recovery voltage slope	15		V/ns
T_{stg}	Storage temperature	–55 to 150		°C
T_j	Max. operating junction temperature	150		°C

1. Limited only by maximum temperature allowed
2. Pulse width limited by safe operating area
3. I_{SD} ≤21 A, di/dt ≤400 A/µs, V_{DD} =80% $V_{(BR)DSS}$

Table 3. Thermal data

Symbol	Parameter	Value					Unit
		TO-220	I²PAK	D²PAK	TO-247	TO-220FP	
$R_{thj\text{-}case}$	Thermal resistance junction-case max	**0.78**				3.1	°C/W
$R_{thj\text{-}pcb}$	Thermal resistance junction-pcb max	**--**	**--**	**30**	**--**	--	
$R_{thj\text{-}amb}$	Thermal resistance junction-ambient max	62.5		--	50	62.5	°C/W
T_l	Maximum lead temperature for soldering purpose	300					°C

Table 4. Avalanche characteristics

Symbol	Parameter	Value	Unit
I_{AR}	Avalanche current, repetitive or not-repetitive (pulse width limited by Tj Max)	10	A
E_{AS}	Single pulse avalanche energy (starting T_J = 25 °C, I_D=I_{AR}, V_{DD} = 50 V)	850	mJ

2 Electrical characteristics

(T_{CASE} = 25 °C unless otherwise specified)

Table 5. On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	I_D = 1 mA, V_{GS} = 0	600			V
dv/dt (1)	Drain source voltage slope	V_{DD} = 480 V, I_D = 21 A, V_{GS} = 10 V		48		V/ns
I_{DSS}	Zero gate voltage drain current (V_{GS} = 0)	V_{DS} = Max rating V_{DS} = Max rating, @125 °C			1 100	µA µA
I_{GSS}	Gate-body leakage current (V_{DS} = 0)	V_{GS} = ± 20 V			100	nA
$V_{GS(th)}$	Gate threshold voltage	V_{DS} = V_{GS}, I_D = 250 µA	2	3	4	V
$R_{DS(on)}$	Static drain-source on resistance	V_{GS} = 10 V, I_D = 10.5 A		0.130	0.160	Ω

1. Characteristic value at turn off on inductive load

Table 6. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
g_{fs} (1)	Forward transconductance	V_{DS}=15 V, I_D =11 A		17		S
C_{iss} C_{oss} C_{rss}	Input capacitance Output capacitance Reverse transfer capacitance	V_{DS} = 50 V, f = 1 MHz, V_{GS} = 0		2400 200 25		pF pF pF
$C_{oss\ eq.}$ (2)	Equivalent output capacitance	V_{GS} = 0, V_{DS} = 0 to 480 V		310		pF
Q_g Q_{gs} Q_{gd}	Total gate charge Gate-source charge Gate-drain charge	V_{DD} = 480 V, I_D =21 A, V_{GS} = 10 V, *(see Figure 19)*		84 14 44		nC nC nC
R_g	Gate input resistance	f=1 MHz Gate DC Bias=0 Test signal level=20 mV open drain		1.6		Ω

1. Pulsed: Pulse duration = 300 µs, duty cycle 1.5%
2. $C_{oss\ eq.}$ is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DS}

Table 7. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	V_{DD} =300 V, I_D = 10 A		24.5		ns
t_r	Rise time	R_G = 4.7 Ω V_{GS} = 10 V		18		ns
$t_{d(off)}$	Turn-off delay time	*(see Figure 18)*		94		ns
t_f	Fall time			24		ns

Table 8. Source drain diode

Symbol	Parameter	Test conditions	Min	Typ.	Max	Unit
I_{SD}	Source-drain current				21	A
I_{SDM} (1)	Source-drain current (pulsed)				84	A
V_{SD} (2)	Forward on voltage	I_{SD} = 21 A, V_{GS} = 0			1.3	V
t_{rr}	Reverse recovery time	I_{SD} = 21 A, di/dt = 100 A/µs		427		ns
Q_{rr}	Reverse recovery charge	V_{DD} = 100 V		7.2		µC
I_{RRM}	Reverse recovery current	*(see Figure 23)*		33.6		A
t_{rr}	Reverse recovery time	I_{SD} = 21 A, di/dt = 100 A/µs		526		ns
Q_{rr}	Reverse recovery charge	V_{DD} = 100 V, T_j = 150 °C		9.1		µC
I_{RRM}	Reverse recovery current	*(see Figure 23)*		34.5		A

1. Pulse width limited by safe operating area
2. Pulsed: Pulse duration = 300 µs, duty cycle 1.5%

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area for TO-220 / D²PAK / I²PAK

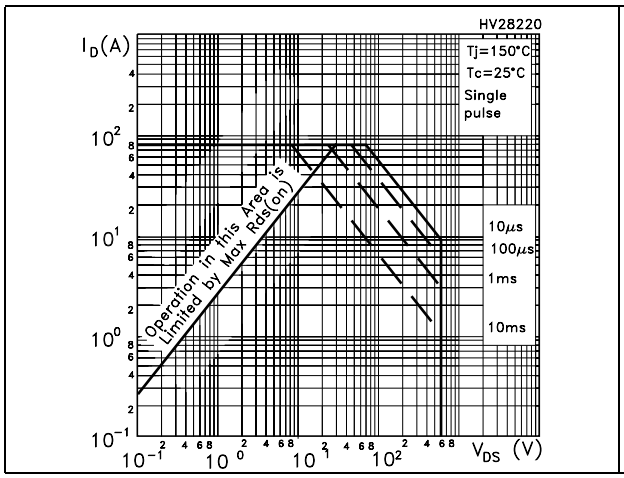


Figure 3. Thermal impedance for TO-220 / D²PAK / I²PAK

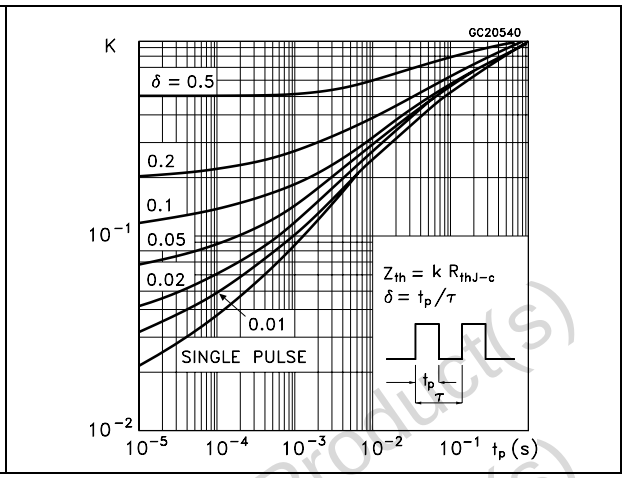


Figure 4. Safe operating area for TO-220FP

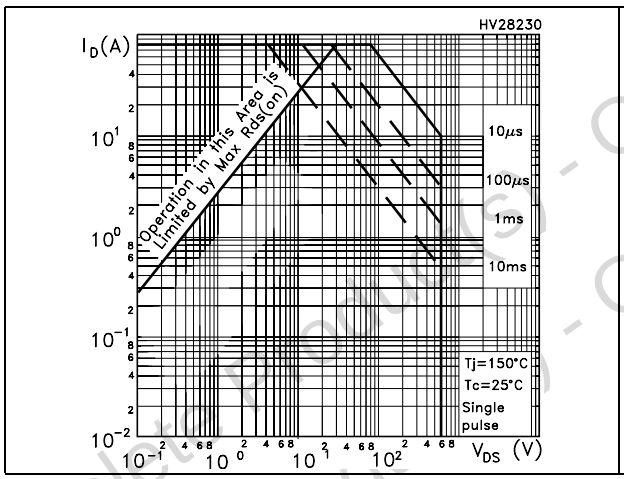


Figure 5. Thermal impedance for TO-220FP

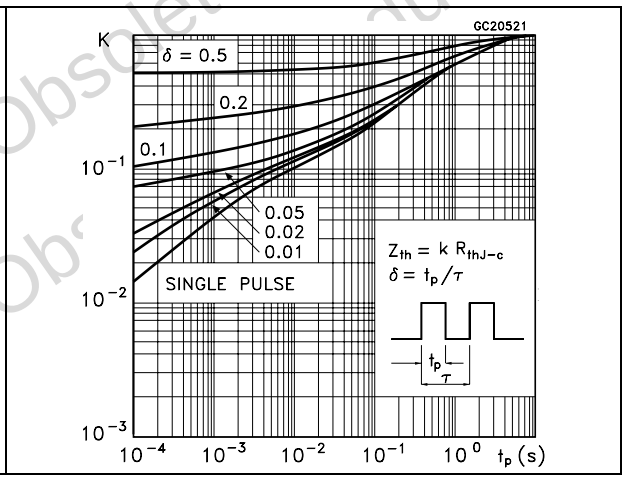


Figure 6. Safe operating area for TO-247

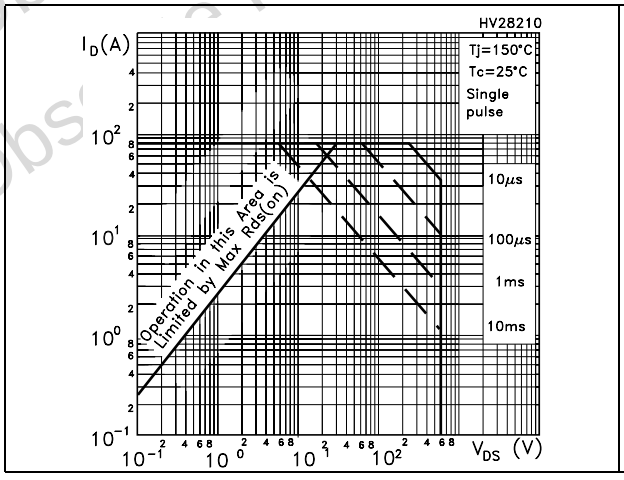


Figure 7. Thermal impedance for TO-247

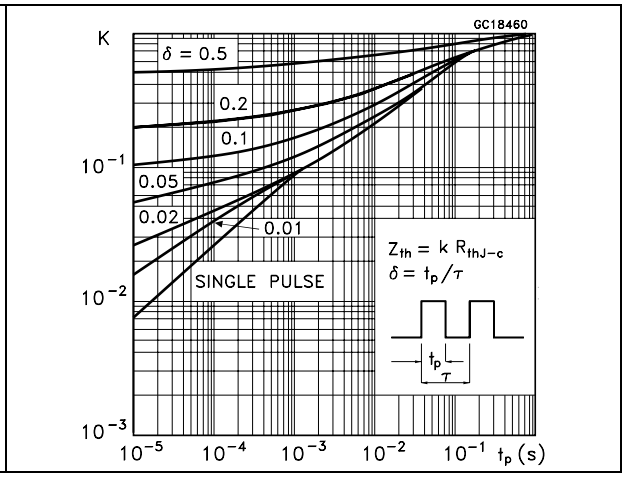


Figure 8. Output characteristics

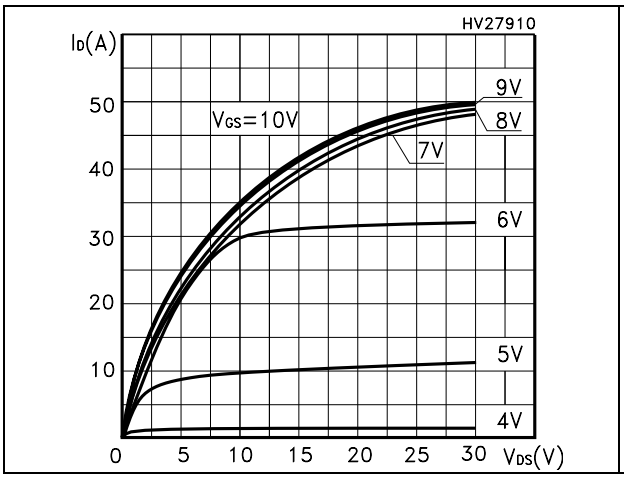


Figure 9. Transfer characteristics

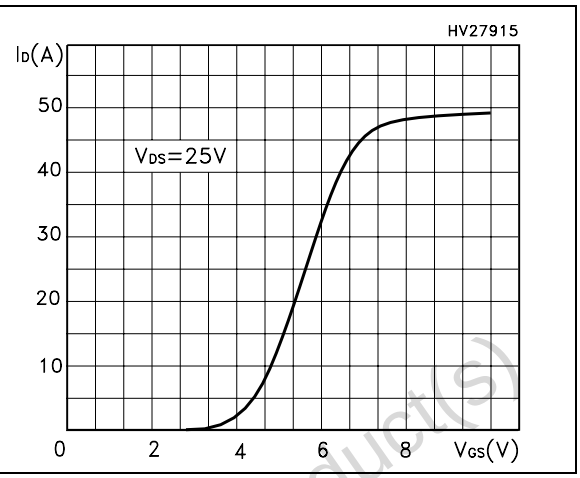


Figure 10. Transconductance

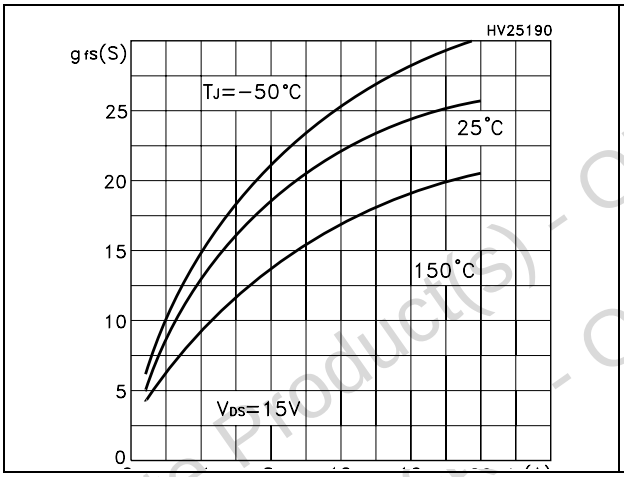


Figure 11. Static drain-source on resistance

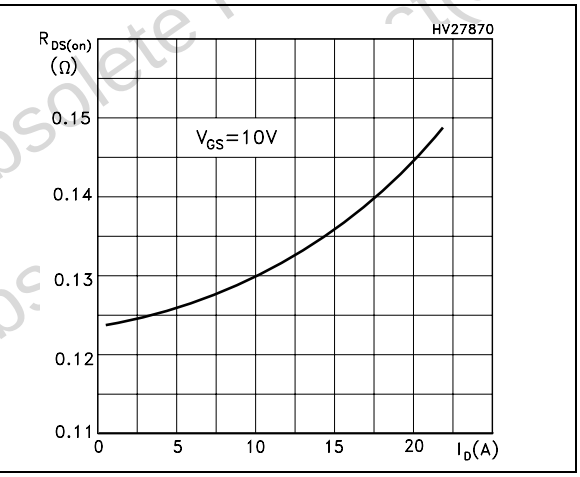


Figure 12. Gate charge vs gate-source voltage

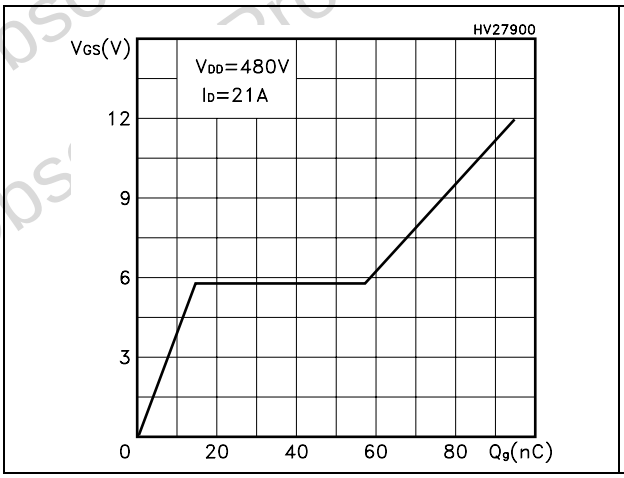


Figure 13. Capacitance variations

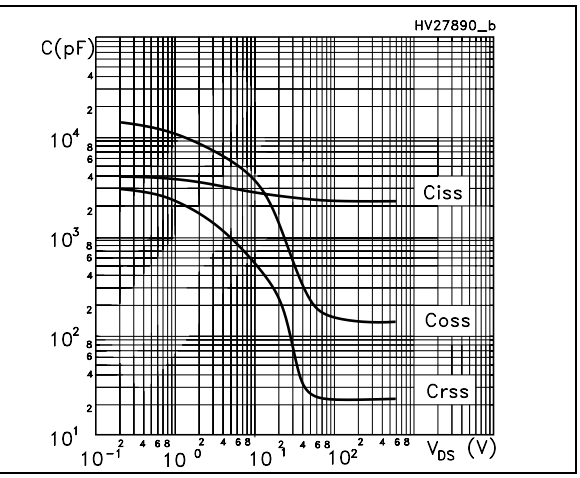


Figure 14. Normalized gate threshold voltage vs temperature

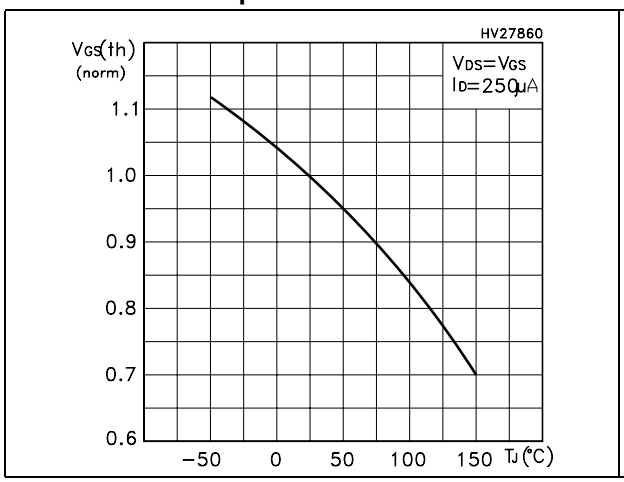


Figure 15. Normalized on resistance vs temperature

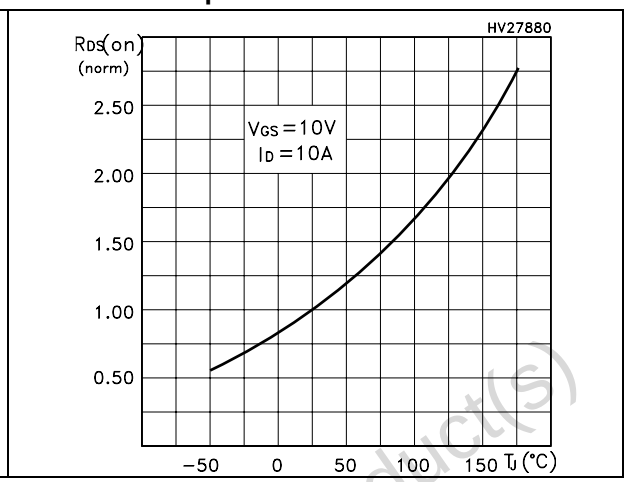


Figure 16. Source-drain diode forward characteristics

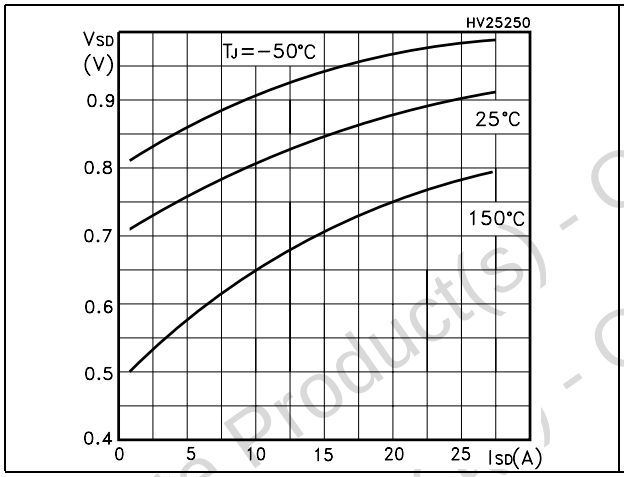
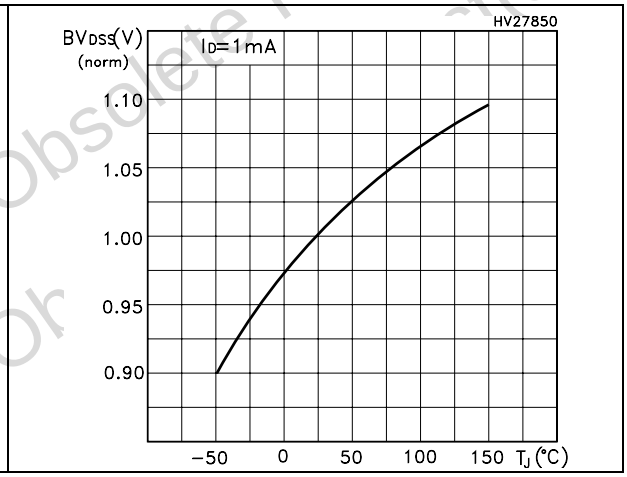


Figure 17. Normalized B_{VDSS} vs temperature



3 Test circuit

Figure 18. Switching times test circuit for resistive load

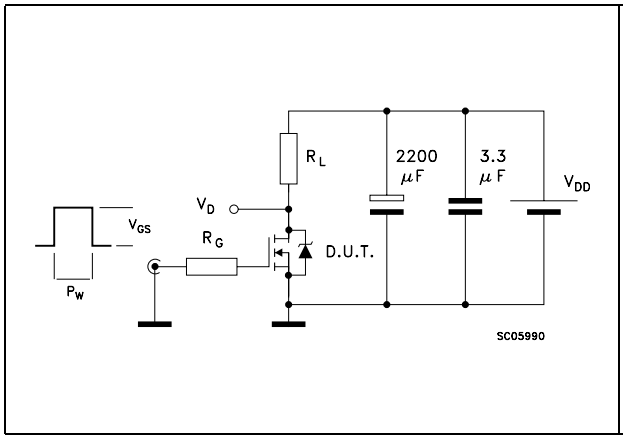


Figure 19. Gate charge test circuit

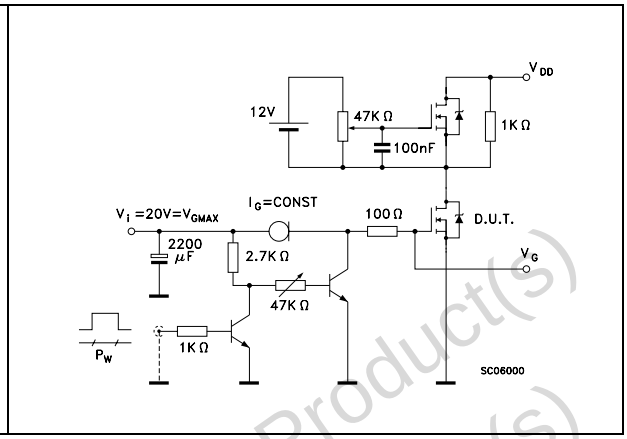


Figure 20. Test circuit for inductive load switching and diode recovery times

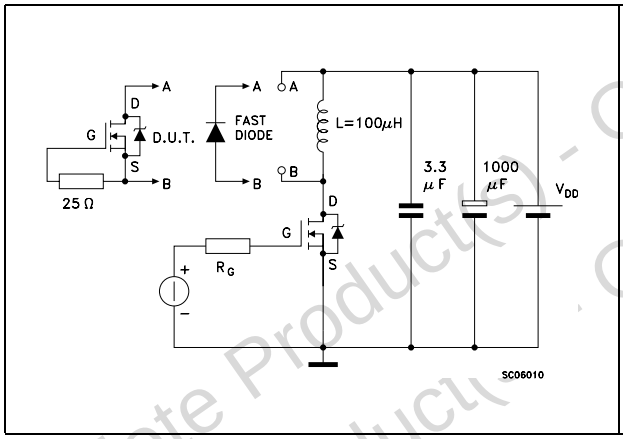


Figure 21. Unclamped Inductive load test circuit

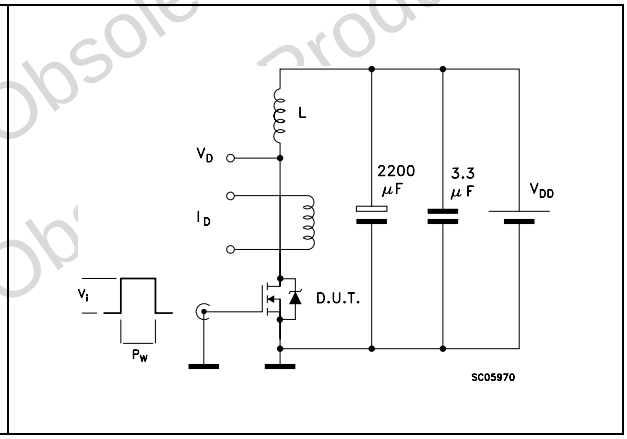


Figure 22. Unclamped inductive waveform

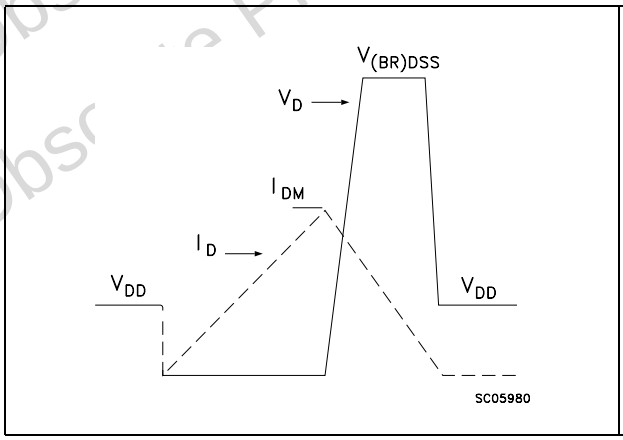
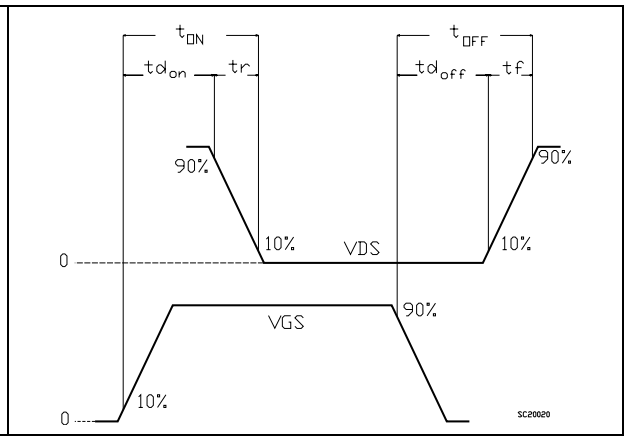


Figure 23. Switching time waveform

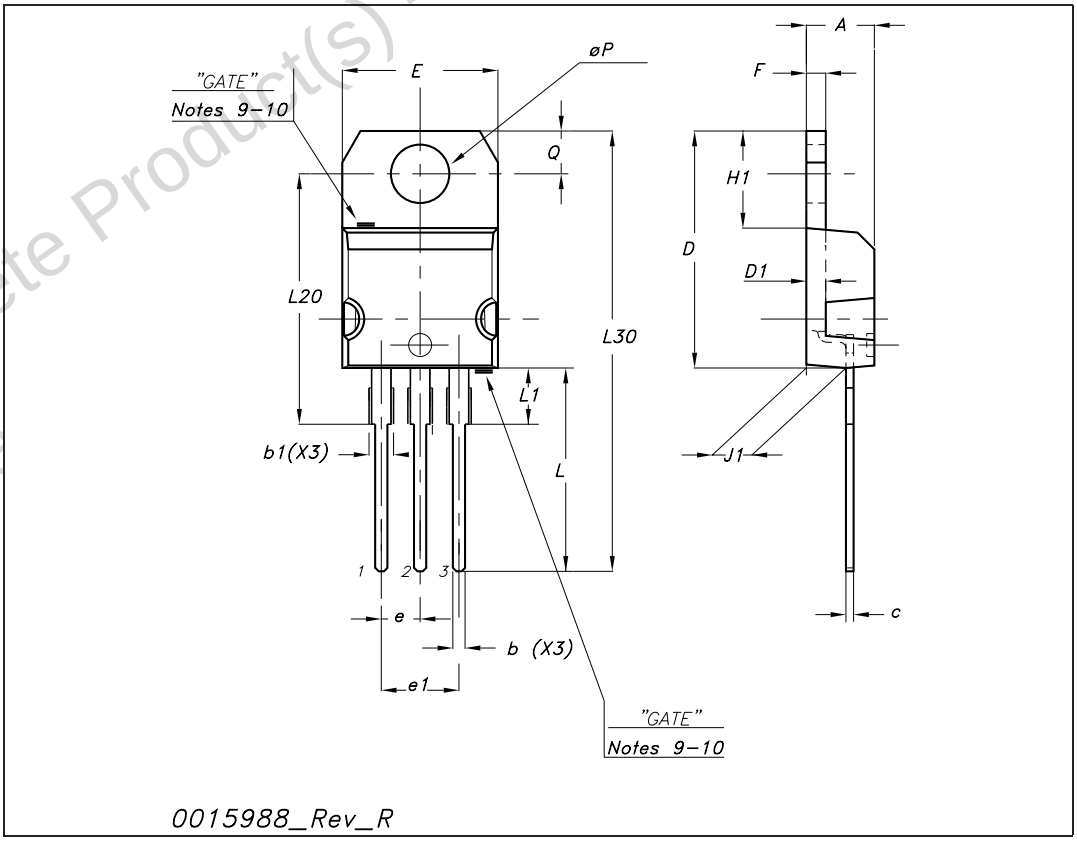


4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: *www.st.com*

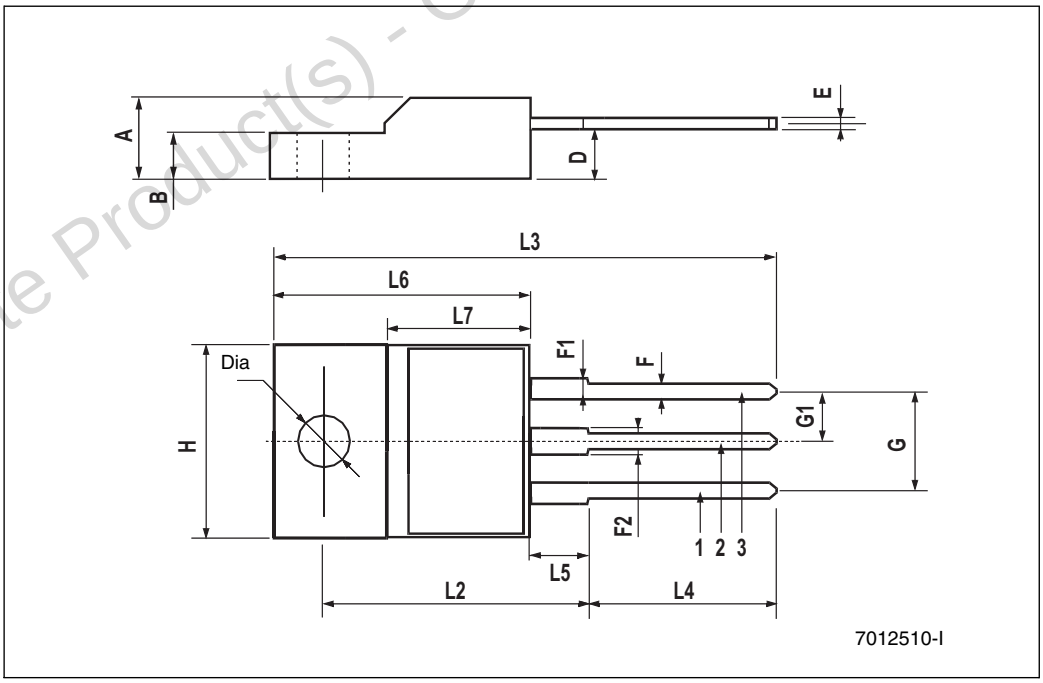
TO-220 mechanical data

Dim	mm			inch		
	Min	Typ	Max	Min	Typ	Max
A	4.40		4.60	0.173		0.181
b	0.61		0.88	0.024		0.034
b1	1.14		1.70	0.044		0.066
c	0.48		0.70	0.019		0.027
D	15.25		15.75	0.6		0.62
D1		1.27			0.050	
E	10		10.40	0.393		0.409
e	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
F	1.23		1.32	0.048		0.051
H1	6.20		6.60	0.244		0.256
J1	2.40		2.72	0.094		0.107
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L20		16.40			0.645	
L30		28.90			1.137	
ØP	3.75		3.85	0.147		0.151
Q	2.65		2.95	0.104		0.116



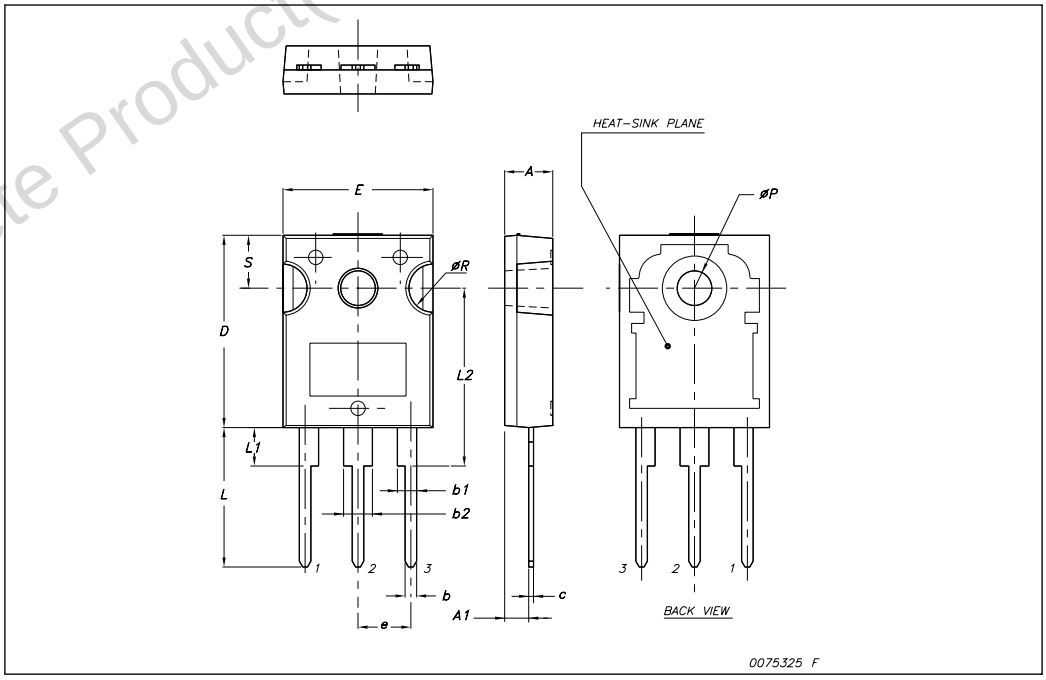
TO-220FP mechanical data

Dim.	mm.			inch		
	Min.	Typ	Max.	Min.	Typ.	Max.
A	4.40		4.60	0.173		0.181
B	2.5		2.7	0.098		0.106
D	2.5		2.75	0.098		0.108
E	0.45		0.70	0.017		0.027
F	0.75		1.00	0.030		0.039
F1	1.15		1.50	0.045		0.067
F2	1.15		1.50	0.045		0.067
G	4.95		5.20	0.195		0.204
G1	2.40		2.70	0.094		0.106
H	10		10.40	0.393		0.409
L2		16			0.630	
L3	28.6		30.6	1.126		1.204
L4	9.80		10.60	0.385		0.417
L5	2.9		3.6	0.114		0.141
L6	15.90		16.40	0.626		0.645
L7	9		9.30	0.354		0.366
Dia	3		3.2	0.118		0.126



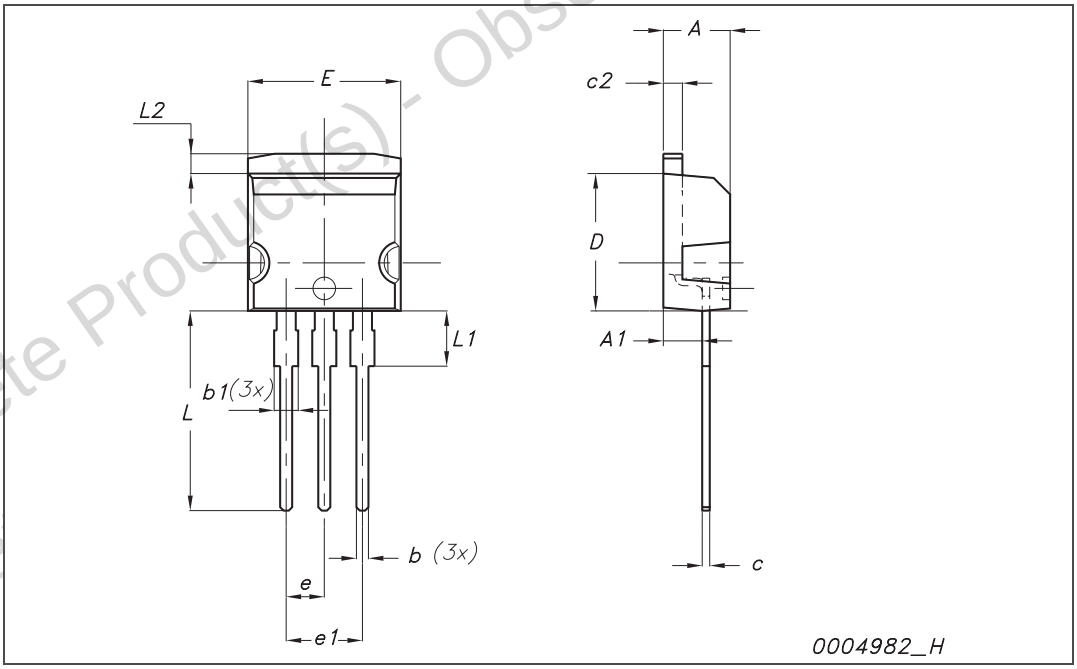
TO-247 Mechanical data

Dim.	mm.		
	Min.	Typ	Max.
A	4.85		5.15
A1	2.20		2.60
b	1.0		1.40
b1	2.0		2.40
b2	3.0		3.40
c	0.40		0.80
D	19.85		20.15
E	15.45		15.75
e		5.45	
L	14.20		14.80
L1	3.70		4.30
L2		18.50	
øP	3.55		3.65
øR	4.50		5.50
S		5.50	



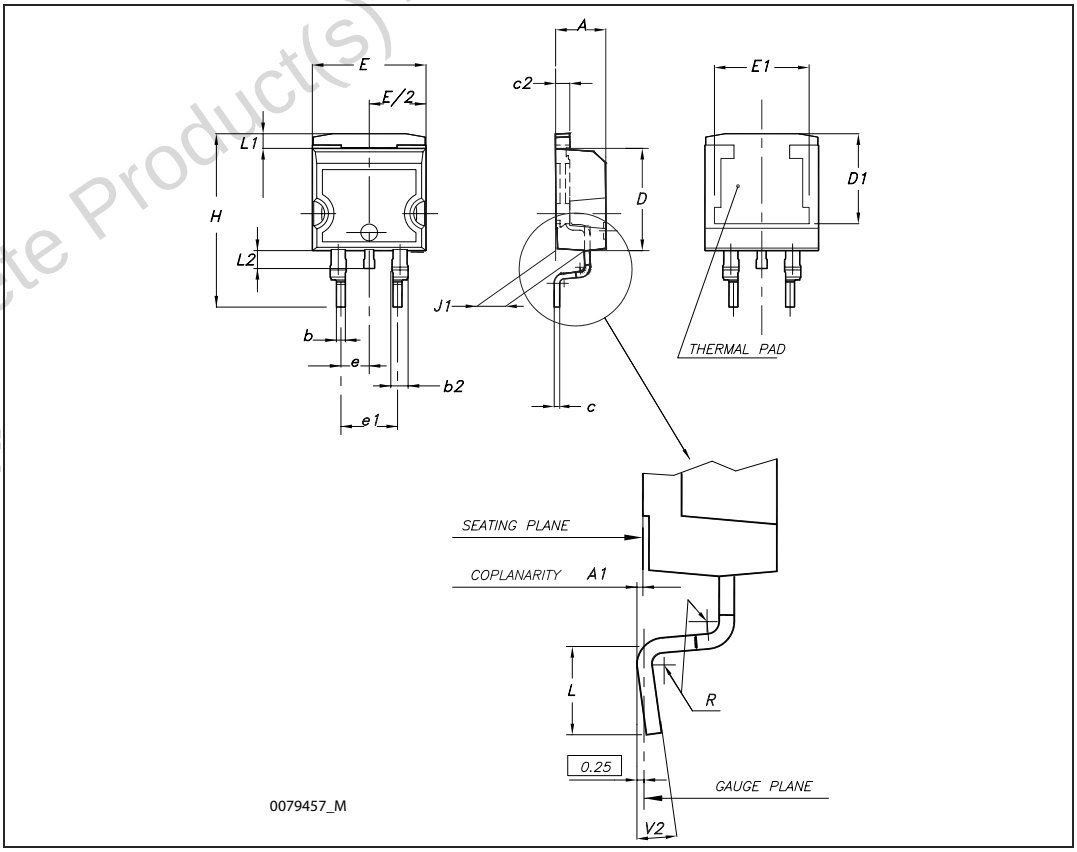
I²PAK (TO-262) mechanical data

Dim	mm			inch		
	Min	Typ	Max	Min	Typ	Max
A	4.40		4.60	0.173		0.181
A1	2.40		2.72	0.094		0.107
b	0.61		0.88	0.024		0.034
b1	1.14		1.70	0.044		0.066
c	0.49		0.70	0.019		0.027
c2	1.23		1.32	0.048		0.052
D	8.95		9.35	0.352		0.368
e	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
E	10		10.40	0.393		0.410
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L2	1.27		1.40	0.050		0.055



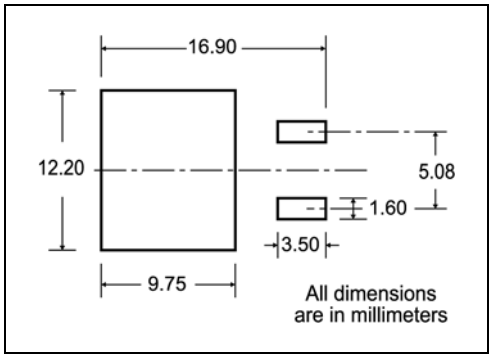
D²PAK (TO-263) mechanical data

Dim	mm			inch		
	Min	Typ	Max	Min	Typ	Max
A	4.40		4.60	0.173		0.181
A1	0.03		0.23	0.001		0.009
b	0.70		0.93	0.027		0.037
b2	1.14		1.70	0.045		0.067
c	0.45		0.60	0.017		0.024
c2	1.23		1.36	0.048		0.053
D	8.95		9.35	0.352		0.368
D1	7.50			0.295		
E	10		10.40	0.394		0.409
E1	8.50			0.334		
e		2.54			0.1	
e1	4.88		5.28	0.192		0.208
H	15		15.85	0.590		0.624
J1	2.49		2.69	0.099		0.106
L	2.29		2.79	0.090		0.110
L1	1.27		1.40	0.05		0.055
L2	1.30		1.75	0.051		0.069
R		0.4			0.016	
V2	0°		8°	0°		8°

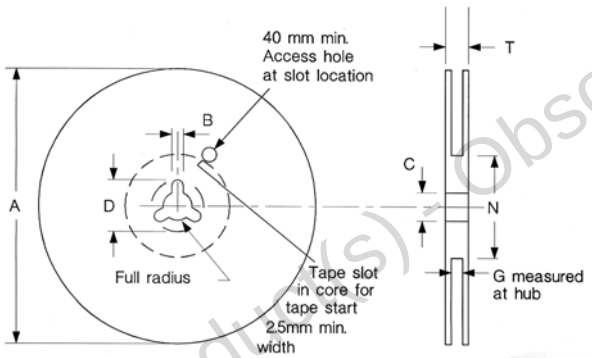


5 Packaging mechanical data

D²PAK FOOTPRINT



TAPE AND REEL SHIPMENT



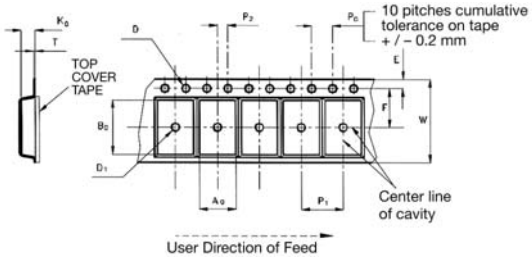
REEL MECHANICAL DATA

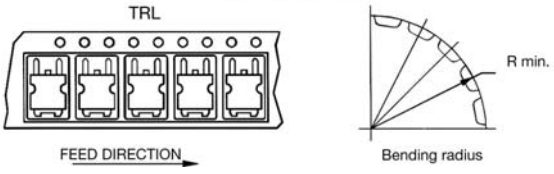
DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A		330		12.992
B	1.5		0.059	
C	12.8	13.2	0.504	0.520
D	20.2		0795	
G	24.4	26.4	0.960	1.039
N	100		3.937	
T		30.4		1.197

BASE QTY	BULK QTY
1000	1000

TAPE MECHANICAL DATA

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A0	10.5	10.7	0.413	0.421
B0	15.7	15.9	0.618	0.626
D	1.5	1.6	0.059	0.063
D1	1.59	1.61	0.062	0.063
E	1.65	1.85	0.065	0.073
F	11.4	11.6	0.449	0.456
K0	4.8	5.0	0.189	0.197
P0	3.9	4.1	0.153	0.161
P1	11.9	12.1	0.468	0.476
P2	1.9	2.1	0.075	0.082
R	50		1.574	
T	0.25	0.35	0.0098	0.0137
W	23.7	24.3	0.933	0.956





* on sales type

6 Revision history

Table 9. Document revision history

Date	Revision	Changes
30-Nov-2004	1	First release.
22-Mar-2005	2	Modified title
23-May-2005	3	Inserted some values in *Table 7*
08-Jun-2005	4	Inserted new row in *Table 6*
08-Sep-2005	5	New value for $C_{oss\ eq}$ in *Table 6*
28-Sep-2005	6	Added curves
26-Oct-2005	7	Complete version
23-Jun-2006	8	New template, new value on *Absolute maximum ratings*
25-Aug-2006	9	Wrong title on first page
14-Nov-2006	10	Modified *Avalanche characteristics*
19-Jan-2007	11	Typo mistake on *Table 7*
11-Jun-2008	12	– Updated $R_{DS(on)}$ max value in *Table 5* – Corrected capacitance value in *Table 6* – Update *Figure 13: Capacitance variations*

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